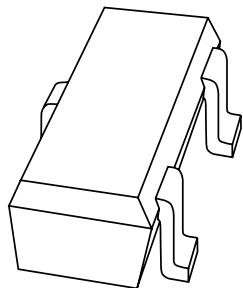


DATA SHEET



PDTC143XK
NPN resistor-equipped transistor;
 $R1 = 4.7 \text{ k}\Omega$, $R2 = 10 \text{ k}\Omega$

Product specification

2002 Jan 15

NPN resistor-equipped transistor; R1 = 4.7 kΩ, R2 = 10 kΩ

PDTC143XK

FEATURES

- Built-in bias resistors
- 250 mW total power dissipation
- Package size 2.9 × 1.5 × 1.15 mm
- Simplification of circuit design
- Reduces number of components and required PCB area.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	50	V
I_o	output current (DC)	100	mA
R1	bias resistor	4.7	kΩ
R2	bias resistor	10	kΩ

PINNING

PIN	DESCRIPTION
1	base/input
2	emitter/ground (+)
3	collector/output

APPLICATIONS

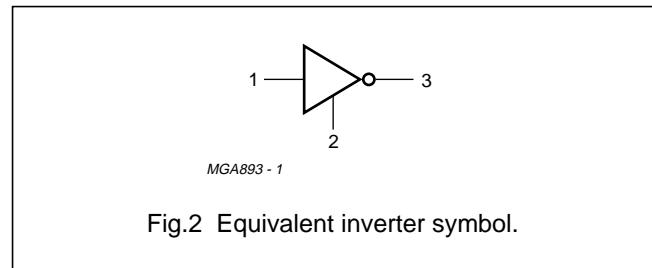
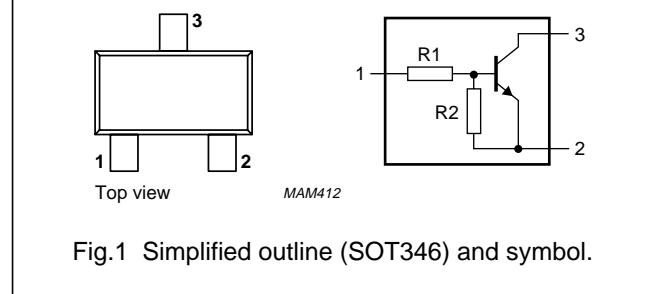
- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

DESCRIPTION

NPN resistor equipped transistor in a SOT346 (SC-59) plastic package.

MARKING

TYPE NUMBER	MARKING CODE
PDTC143XK	26



NPN resistor-equipped transistor;
 R1 = 4.7 kΩ, R2 = 10 kΩ

PDTC143XK

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	50	V
V _{CEO}	collector-emitter voltage	open base	–	50	V
V _{EBO}	emitter-base voltage	open collector	–	10	V
V _i	input voltage positive negative		– –	+20 –7	V V
I _O	output current (DC)		–	100	mA
I _{CM}	peak collector current		–	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	250	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. For mounting conditions, see "Thermal considerations and footprint design for SOT346 in the SC18 Data Handbook".

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	in free air; note 1	500	K/W

Note

1. For mounting conditions, see "Thermal considerations and footprint design for SOT346 in the SC18 Data Handbook".

NPN resistor-equipped transistor;
 $R1 = 4.7 \text{ k}\Omega$, $R2 = 10 \text{ k}\Omega$

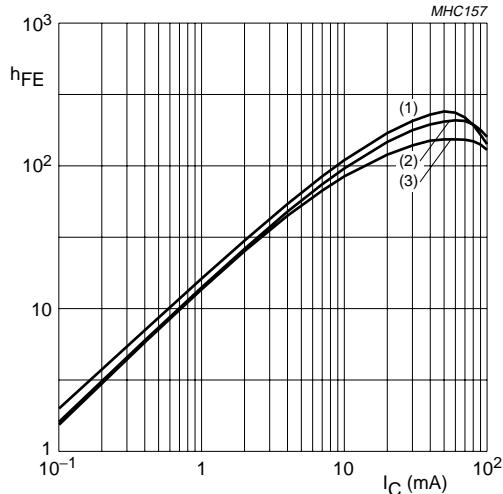
PDTC143XK

CHARACTERISTICS $T_{\text{amb}} = 25 \text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$V_{\text{CB}} = 50 \text{ V}$; $I_E = 0$	—	—	100	nA
I_{CEO}	collector-emitter cut-off current	$V_{\text{CE}} = 30 \text{ V}$; $I_B = 0$	—	—	1	μA
		$V_{\text{CE}} = 30 \text{ V}$; $I_B = 0$; $T_j = 150 \text{ }^{\circ}\text{C}$	—	—	50	μA
I_{EBO}	emitter-base cut-off current	$V_{\text{EB}} = 5 \text{ V}$; $I_C = 0$	—	—	0.6	mA
h_{FE}	DC current gain	$V_{\text{CE}} = 5 \text{ V}$; $I_C = 10 \text{ mA}$	50	—	—	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}$; $I_B = 0.5 \text{ mA}$	—	—	100	mV
$V_{i(\text{off})}$	input off voltage	$V_{\text{CE}} = 5 \text{ V}$; $I_C = 100 \mu\text{A}$	—	—	0.3	V
$V_{i(\text{on})}$	input on voltage	$V_{\text{CE}} = 0.3 \text{ V}$; $I_C = 20 \text{ mA}$	2.5	—	—	V
$R1$	input resistor		3.3	4.7	6.1	$\text{k}\Omega$
$\frac{R2}{R1}$	resistor ratio		1.7	2.1	2.6	
C_c	collector capacitance	$I_E = i_e = 0$; $V_{\text{CB}} = 10 \text{ V}$; $f = 1 \text{ MHz}$	—	—	3	pF

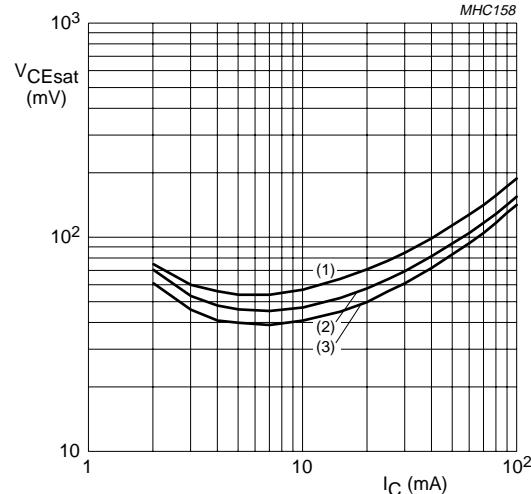
NPN resistor-equipped transistor;
 R1 = 4.7 k Ω , R2 = 10 k Ω

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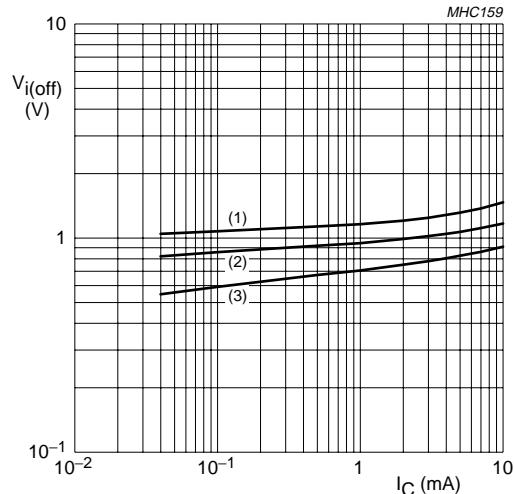
$V_{CE} = 5$ V.
 (1) $T_{amb} = 100$ °C.
 (2) $T_{amb} = 25$ °C.
 (3) $T_{amb} = -40$ °C.

Fig.3 DC current gain as a function of collector current; typical values.



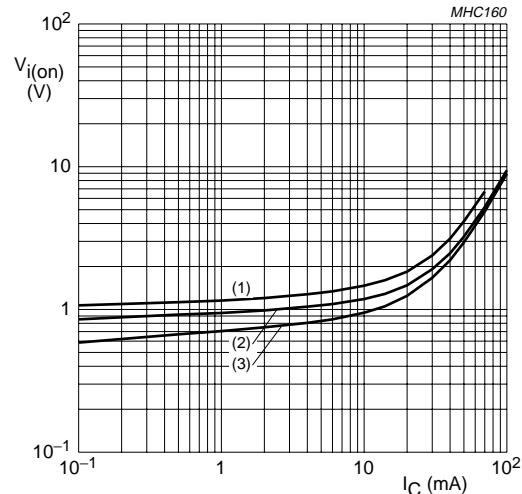
$I_C/I_B = 20$.
 (1) $T_{amb} = 100$ °C.
 (2) $T_{amb} = 25$ °C.
 (3) $T_{amb} = -40$ °C.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



$V_{CE} = 5$ V.
 (1) $T_{amb} = -40$ °C.
 (2) $T_{amb} = 25$ °C.
 (3) $T_{amb} = 100$ °C.

Fig.5 Input-off voltage as a function of collector current; typical values.



$V_{CE} = 0.3$ V.
 (1) $T_{amb} = -40$ °C.
 (2) $T_{amb} = 25$ °C.
 (3) $T_{amb} = 100$ °C.

Fig.6 Input-on voltage as a function of collector current; typical values.

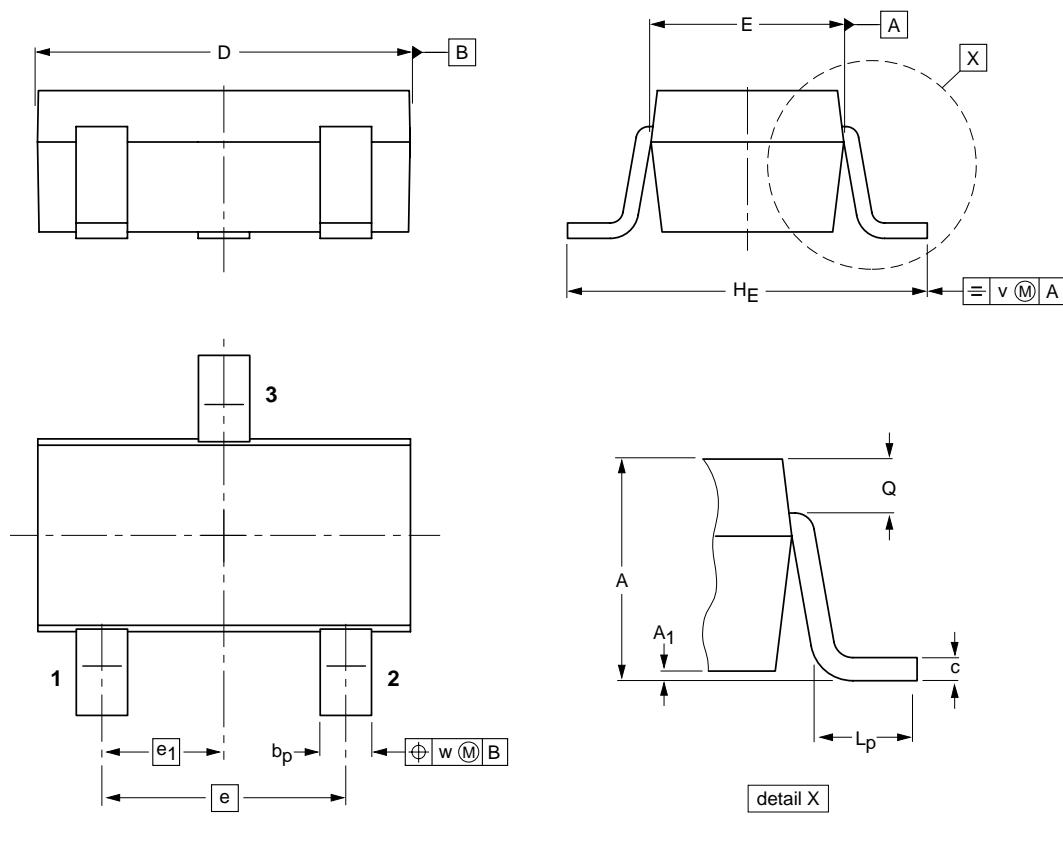
NPN resistor-equipped transistor;
 R1 = 4.7 kΩ, R2 = 10 kΩ

PDTC143XK

PACKAGE OUTLINE

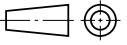
Plastic surface mounted package; 3 leads

SOT346



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b _p	c	D	E	e	e ₁	H _E	l _p	Q	v	w
mm	1.3	0.1	0.50	0.26	3.1	1.7	1.9	0.95	3.0	0.6	0.33	0.2	0.2
	1.0	0.013	0.35	0.10	2.7	1.3	1.9	0.95	2.5	0.2	0.23		

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT346		TO-236	SC-59			98-07-17

NPN resistor-equipped transistor;
 R1 = 4.7 kΩ, R2 = 10 kΩ

PDTC143XK

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